



## 1.0A Glass Passivated Surface Mount Efficient Fast Rectifiers - 50-600V

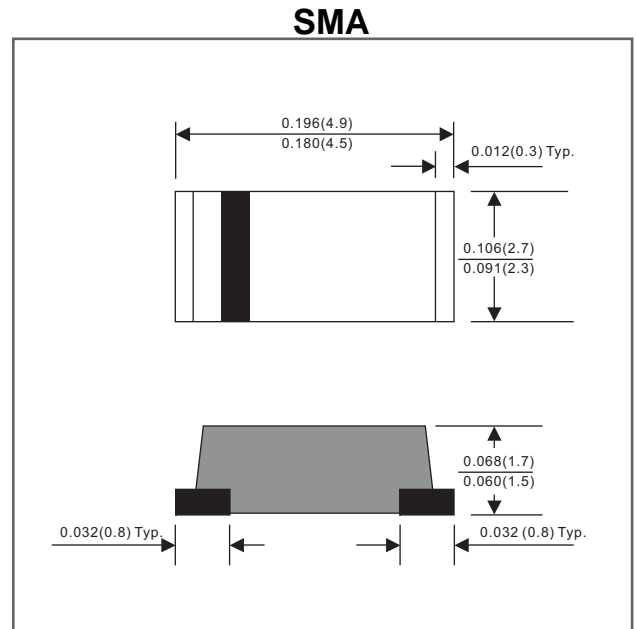
### Package outline

#### Features

- Batch process design, excellent power dissipation offers better reverse leakage current and thermal resistance.
- Low profile surface mounted application in order to optimize board space.
- Tiny plastic SMD package.
- High current capability.
- Fast switching for high efficiency.
- High surge current capability.
- Glass passivated chip junction.
- Lead- free parts meet RoHS requirements.
- Suffix "-H" indicates Halogen-free parts, ex. FMEG101DG-H.

#### Mechanical data

- Epoxy: UL94-V0 rated frame retardant
- Case: Molded plastic, DO-214AC / SMA
- Terminals: Plated terminals, solderable per MIL-STD-750, Method 2026
- Polarity: Indicated by cathode band
- Mounting Position: Any
- Weight: Approximated 0.05 gram



Dimensions in inches and (millimeters)

#### Maximum ratings (AT $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Forward rectified current	Ambient temperature = $55^\circ\text{C}$	$I_O$			1.0	A
Forward surge current	8.3ms single half sine-wave superimposed on rate load (JEDEC methode)	$I_{FSM}$			30	A
Reverse current	$V_R = V_{RRM}$ $T_J = 25^\circ\text{C}$	$I_R$			5.0	$\mu\text{A}$
	$V_R = V_{RRM}$ $T_J = 125^\circ\text{C}$				100	
Diode junction capacitance	f=1MHz and applied 4V DC reverse voltage	$C_J$		15		pF
Storage temperature		$T_{STG}$	-65		+175	$^\circ\text{C}$

SYMBOLS	$V_{RRM}^{*1}$ (V)	$V_{RMS}^{*2}$ (V)	$V_R^{*3}$ (V)	$V_F^{*4}$ (V)	$T_{RR}^{*5}$ (nS)	Operating temperature $T_J$ , ( $^\circ\text{C}$ )
FMEG101DG	50	35	50	0.875	25	-55 to +150
FMEG102DG	100	70	100			
FMEG103DG	200	140	200			
FMEG105DG	400	280	400	1.25		
FMEG105DG	600	420	600	1.75		

\*1 Repetitive peak reverse voltage

\*2 RMS voltage

\*3 Continuous reverse voltage

\*4 Maximum forward voltage@ $I = 1_r, 0A$

\*5 Reverse recovery time , note 1

Note 1. Reverse recovery time test condition,  $I_F=0.5A$ ,  $I_R=1.0A$ ,  $I_{RR}=0.25A$

## Rating and characteristic curves

FIG.1-TYPICAL FORWARD CHARACTERISTICS

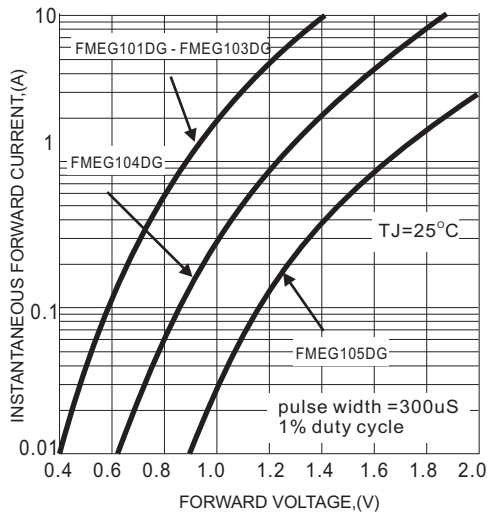


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

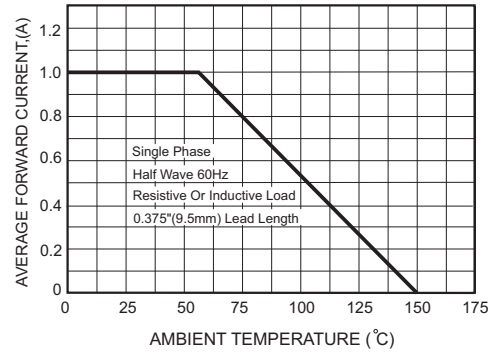
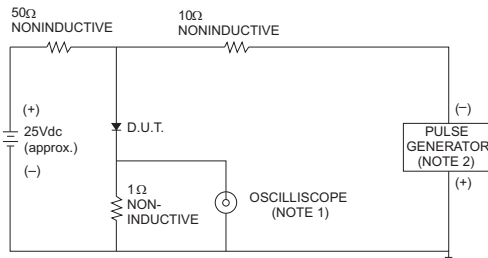


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time = 7ns max., Input Impedance = 1 megohm, 22pF.  
2. Rise Time = 10ns max., Source Impedance = 50 ohms.

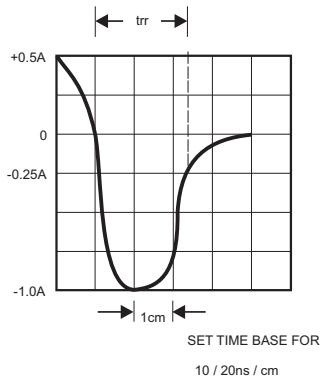


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

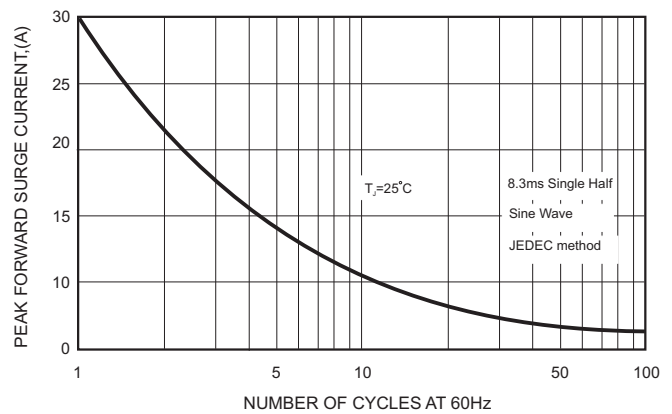


FIG.5-TYPICAL JUNCTION CAPACITANCE

